



P-Channel Enhancement Mode Field Effect Transistor

Product Summary

- V_{DS} -20V
- I_D -55A
- $R_{DS(ON)}$ (at $V_{GS} = -4.5V$) <8.3mohm
- $R_{DS(ON)}$ (at $V_{GS} = -2.5V$) <10.0mohm
- $R_{DS(ON)}$ (at $V_{GS} = -1.8V$) <15.0mohm
-

■ Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-20			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-20V, V_{GS}=0V$			-1	μA
		$V_{DS}=-20V, V_{GS}=0V, T_J=150^\circ\text{C}$			-100	
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 10V, V_{DS}=0V$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-0.4	-0.62	-1.0	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=-4.5V, I_D=-15A$		6.5	8.3	m Ω
		$V_{GS}=-2.5V, I_D=-10A$		8.0	10.0	
		$V_{GS}=-1.8V, I_D=-8.0A$		10.3	15.0	
Diode Forward Voltage	V_{SD}	$I_S=-20A, V_{GS}=0V$		-0.7	-1.2	V
Maximum Body-Diode Continuous Current	I_S				-55	A
Gate resistance	R_g	F=1 MHz, Open drain		7.1		Ω
Dynamic Parameters						
Input Capacitance	C_{iss}	$V_{DS}=-10V, V_{GS}=0V, f=1\text{MHz}$		6358		pF
Output Capacitance	C_{oss}			690		
Reverse Transfer Capacitance	C_{rss}			477		
Switching Parameters						
Total Gate Charge	Q_g	$V_{GS}=-10V, V_{DS}=-15V, I_D=-9.1A$		149		nC
Gate-Source Charge	Q_{gs}			12.7		
Gate-Drain Charge	Q_{gd}			21		
Reverse Recovery Charge	Q_{rr}	$I_F=-6A, di/dt=100A/\mu s$		25.2		ns
Reverse Recovery Time	t_{rr}			46		
Turn-on Delay Time	$t_{D(on)}$	$V_{GS}=-10V, V_{DD}=-15V, I_D=-6A$ $R_{GEN}=2.5\Omega$		11		ns
Turn-on Rise Time	t_r			36		
Turn-off Delay Time	$t_{D(off)}$			182		
Turn-off fall Time	t_f			191		

A. Pulse Test: Pulse Width $\leq 300\mu s$, Duty cycle $\leq 2\%$.B. $T_J=25^\circ\text{C}$, $V_{DD}=20V$, $V_G=10V$, $L=0.5\text{mH}$, $I_{AS}=17.4A$ C. The value of $R_{\theta JA}$ is measured with the device mounted on 1in2 FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The maximum allowed junction temperature of 150°C . The value in any given application depends on the user's specific board design.

Typical Performance Characteristics

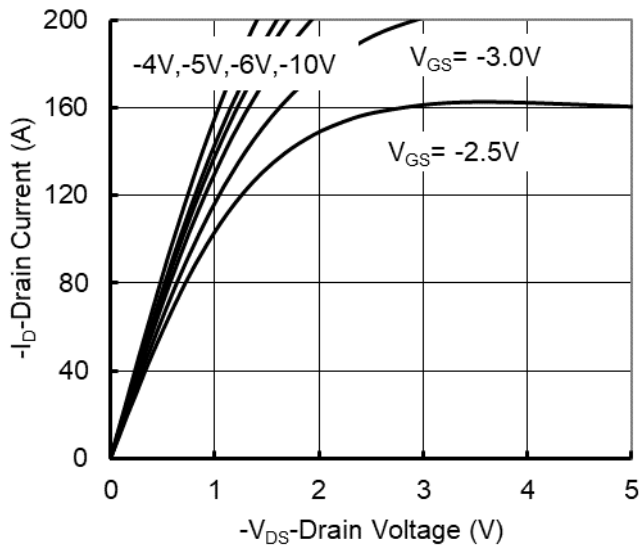


Figure 1. Output Characteristics

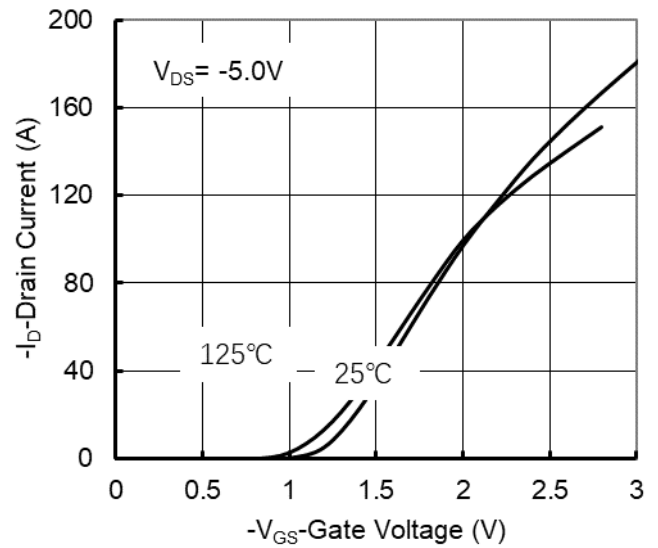


Figure 2. Transfer Characteristics

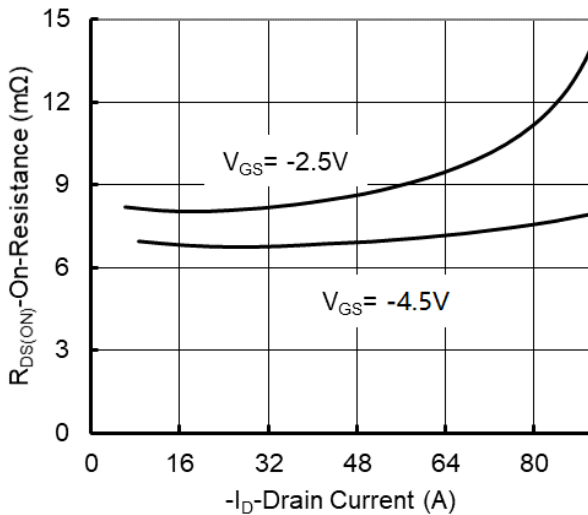


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

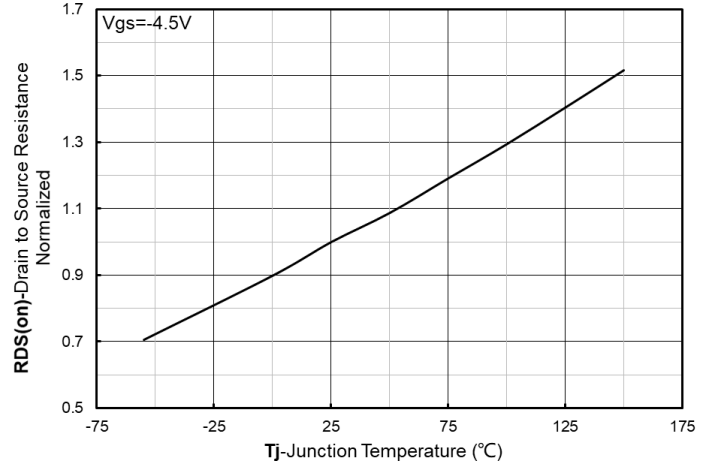


Figure 4. On-Resistance vs. Junction Temperature

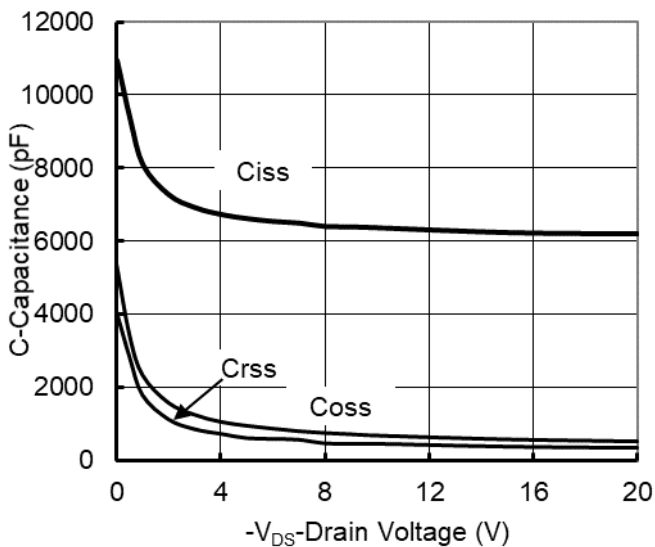


Figure 5. Capacitance Characteristics

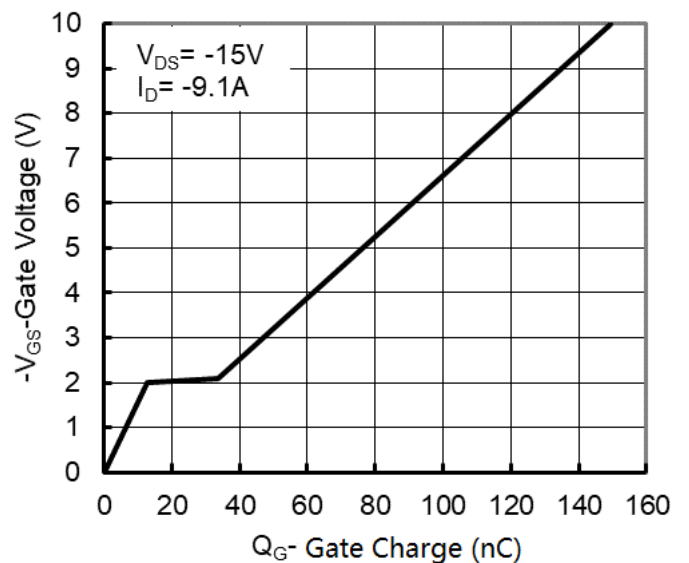


Figure 6. Gate Charge

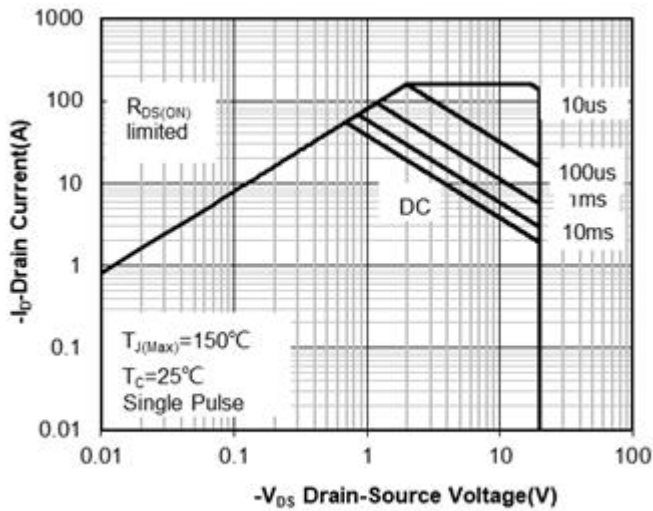


Figure 7. Safe Operation Area

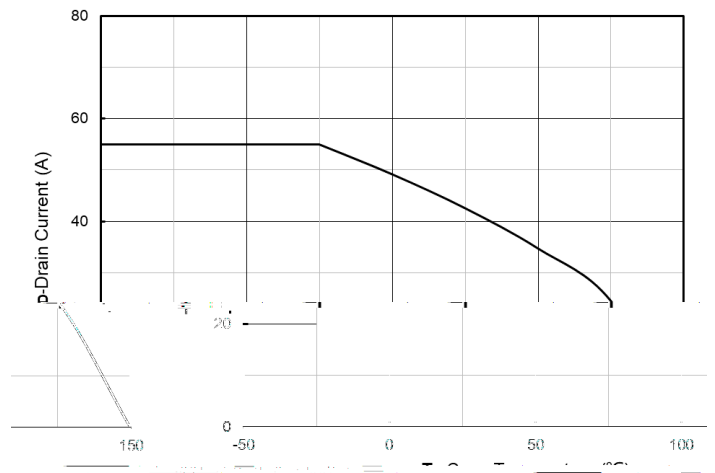


Figure 8. Current dissipation

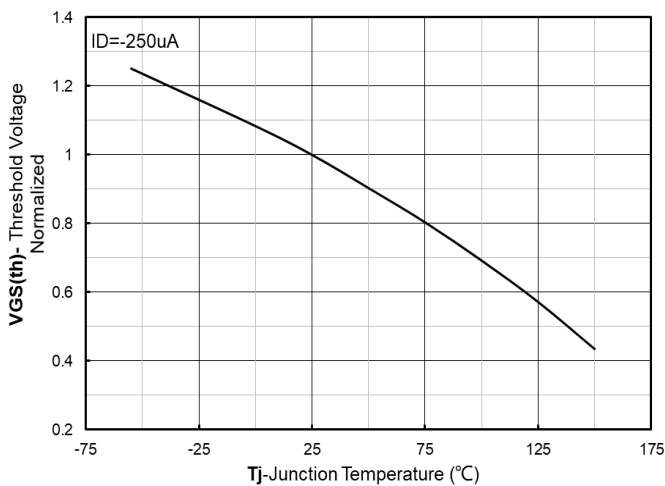


Figure 9. Normalized Threshold voltage

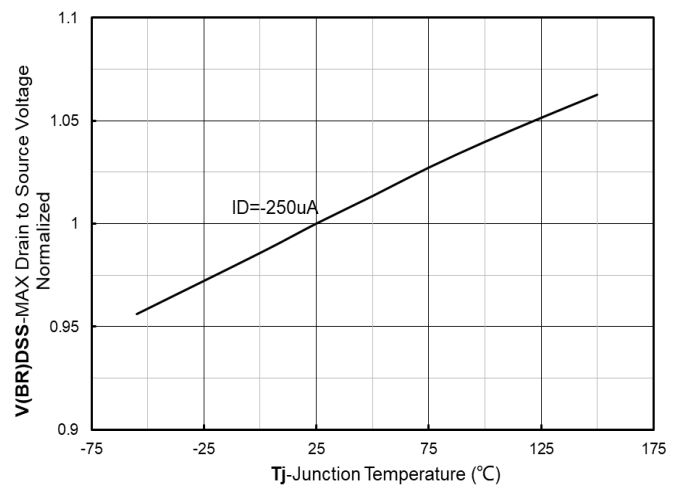


Figure 10. Normalized breakdown voltage

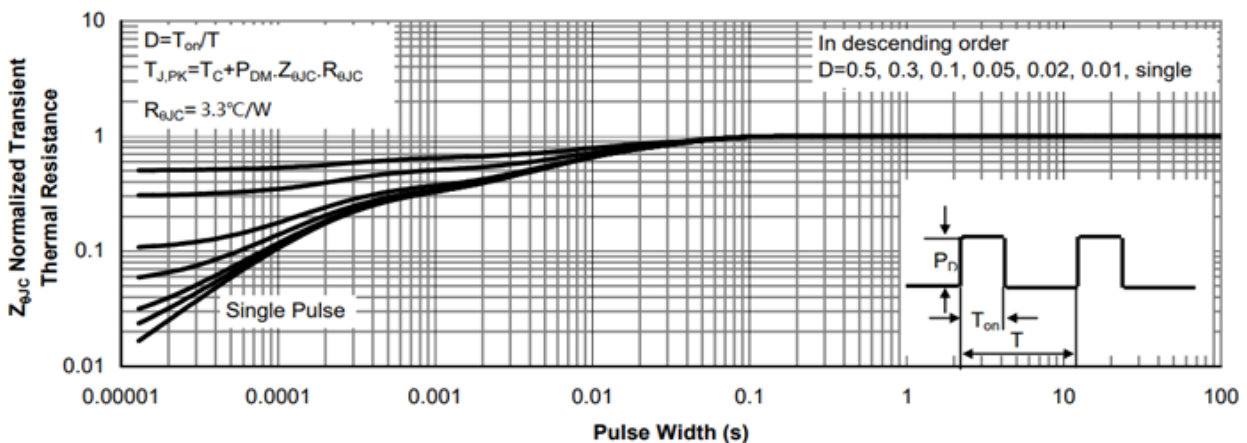
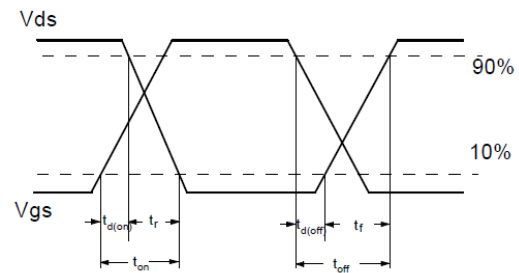
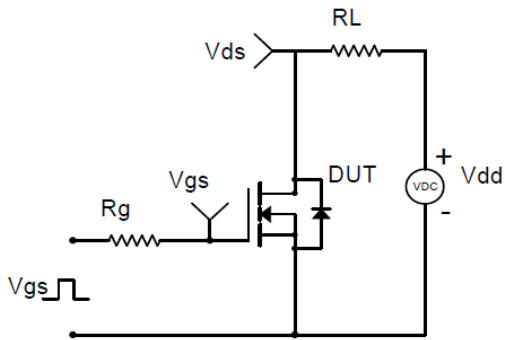
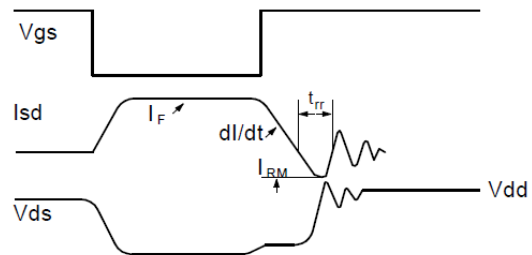
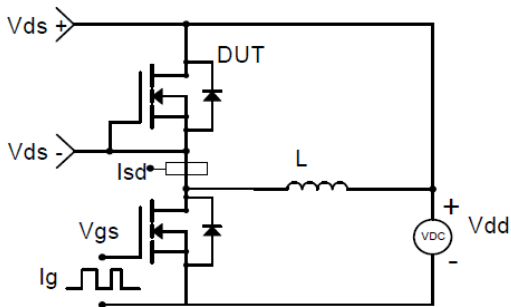


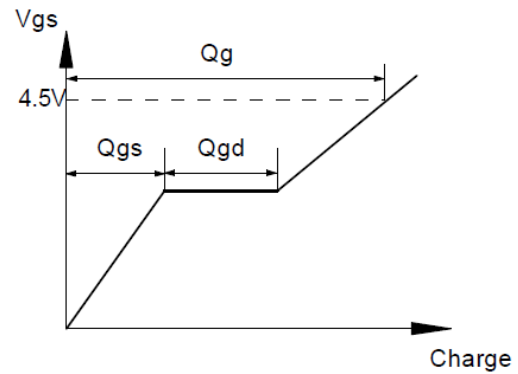
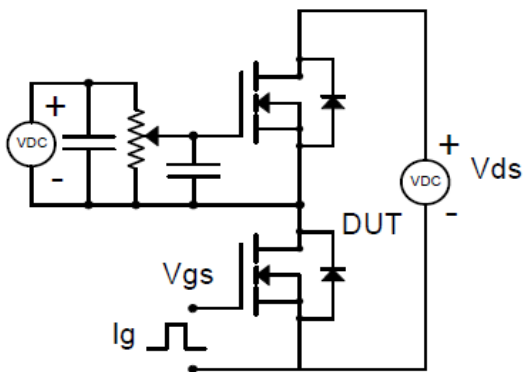
Figure 11. Normalized Maximum Transient Thermal Impedance



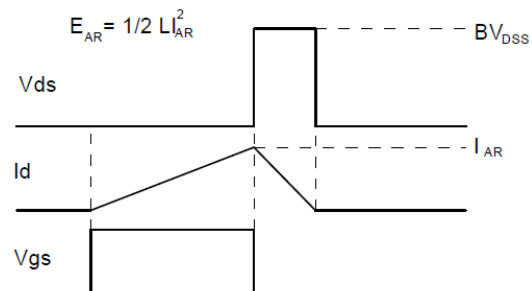
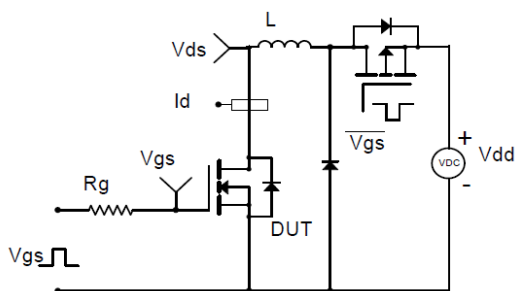
Resistive Switching Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

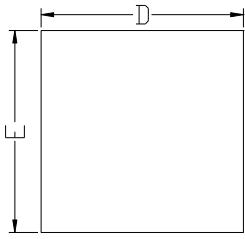


Gate Charge Test Circuit & Waveform

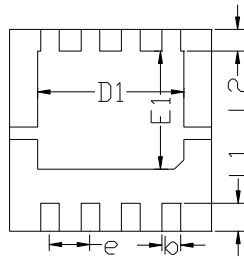


Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

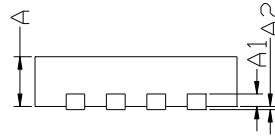
■DFN3333-8L Package information



Top View
正面视图

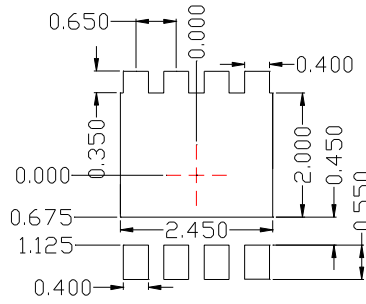


Bottom View
背面视图



Side View
侧面视图

SYMBOL	MILLIMETER		
	MIN	NOM	MAX
D	3.15	3.25	3.35
E	3.15	3.25	3.35
A	0.70	0.80	0.90
A1	0.20 BSC		
A2			0.10
D1	2.20	2.35	2.50
E1	1.80	1.90	2.00
L1	0.35	0.45	0.55
L2	0.35 BSC		
b	0.20	0.30	0.40
e	0.65 BSC		



Suggested Solder Pad Layout
Top View

Note:

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.10\text{mm}$.
3. The pad layout is for reference purposes only.



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